March 2007



## LME49710 High Performance, High Fidelity Audio Operational Amplifier

#### **General Description**

The LME49710 is part of the ultra-low distortion, low noise. high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49710 audio operational amplifiers deliver superior audio signal amplification for outstanding audio performance. The LME49710 combines extremely low voltage noise density (2.5nV/Hz) with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49710 has a high slew rate of ±20V/µs and an output current capability of ±26mA. Further, dynamic range is maximized by an output stage that drives  $2k\Omega$  loads to within 1V of either power supply voltage and to within 1.4V when driving  $600\Omega$  loads.

The LME49710's outstanding CMRR(120dB), PSRR(120dB), and  $V_{OS}$  (0.05mV) give the amplifier excellent operational amplifier DC performance.

The LME49710 has a wide supply range of  $\pm 2.5V$  to  $\pm 17V$ . Over this supply range the LME49710's input circuitry maintains excellent common-mode and power supply rejection, as well as maintaining its low input bias current. The LME49710 is unity gain stable. The Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49710 is available in 8–lead narrow body SOIC, 8– lead plastic DIP, and 8–lead metal can TO-99. Demonstration boards are available for each package.

## **Key Specifications**

Power Supply Voltage Range	±2.5V to ±17V
----------------------------	---------------

• THD+N ( $A_V = 1$ ,  $V_{OUT} = 3V_{RMS}$ ,  $f_{IN} = 1$ kHz)

$R_L = 2k\Omega$	0.00003% (typ)
R <sub>L</sub> = 600Ω	0.00003% (typ)
Input Noise Density	2.5nV/√Hz (typ)
Slew Rate	±20V/μs (typ)
Gain Bandwidth Product	55MHz (typ)
<ul> <li>Open Loop Gain (R<sub>L</sub> = 600Ω)</li> </ul>	140dB (typ)
Input Bias Current	7nA (typ)
Input Offset Voltage	0.05mV (typ)
DC Gain Linearity Error	0.000009%

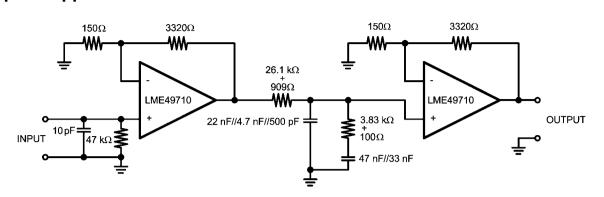
#### **Features**

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 120dB (typ)
- SOIC, DIP, TO-99 metal can packages

#### Applications

- Ultra high quality audio amplification
- High fidelity preamplifiers
- High fidelity multimedia
- State of the art phono pre amps
- High performance professional audio
- High fidelity equalization and crossover networks
- High performance line drivers
- High performance line receivers
- High fidelity active filters

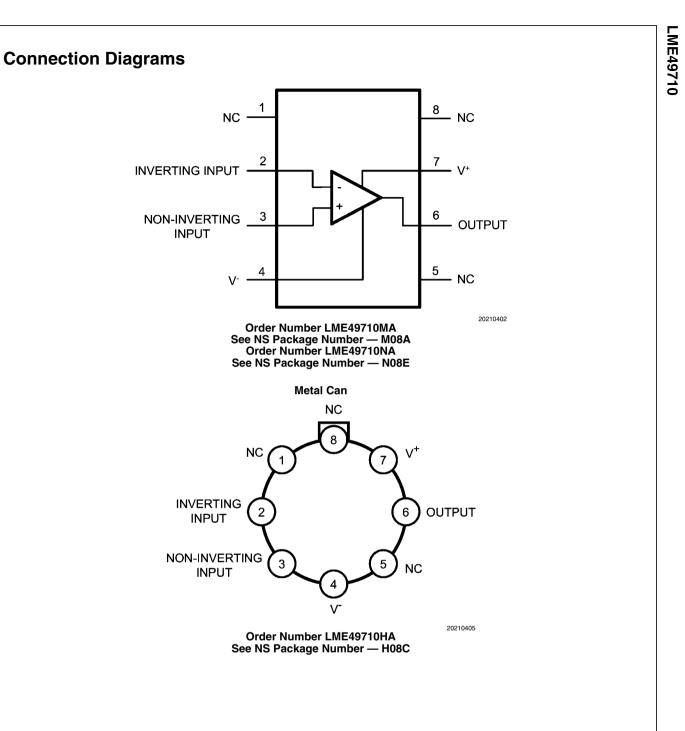
## **Typical Application**



Note: 1% metal film resistors, 5% polypropylene capacitors

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#### FIGURE 1. Passively Equalized RIAA Phono Preamplifier



#### Absolute Maximum Ratings (Notes 1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

36V
–65°C to 150°C
(V-) - 0.7V to (V+) + 0.7V
Continuous
Internally Limited
2000V

200V
150°C
145°C/W
102°C/W
150°C/W
35°C/W
$-40^{\circ}C \le T_A \le 85^{\circ}C$
$\pm 2.5 V \le V_S \le \pm 17 V$

### Electrical Characteristics (Notes 1, 2)

The following specifications apply for  $V_S = \pm 15V$ ,  $R_L = 2k\Omega$ ,  $f_{IN} = 1kHz$ , and  $T_A = 25^{\circ}C$ , unless otherwise specified.

Symbol	Parameter	Conditions	LME49710		
			Typical	Limit	Units
			(Note 6)	(Notes 7, 8)	(Limits)
		$A_V = 1, V_{OUT} = 3V_{RMS}$			
THD+N	Total Harmonic Distortion + Noise	$R_L = 2k\Omega$	0.00003		% (max)
		R <sub>L</sub> = 600Ω	0.00003	0.00009	% (max)
IMD	Intermodulation Distortion	A <sub>V</sub> = 1, V <sub>OUT</sub> = 3V <sub>RMS</sub> Two-tone, 60Hz & 7kHz 4:1	0.00005		% (max)
GBWP	Gain Bandwidth Product		55	45	MHz (min
SR	Slew Rate		±20	±15	V/µs (min)
FPBW	Full Power Bandwidth	$V_{OUT} = 1V_{P-P}, -3dB$ referenced to output magnitude at f = 1kHz	10		MHz
t <sub>s</sub>	Settling time	$A_V = 1$ , 10V step, $C_L = 100 pF$ 0.1% error range	1.2		μs
	Equivalent Input Noise Voltage	f <sub>BW</sub> = 20Hz to 20kHz	0.34	0.65	μV <sub>RMS</sub>
e <sub>n</sub>	Equivalent Input Noise Density	f = 1kHz	2.5	4.7	nV/√Hz
		f = 10Hz	6.4		nVI√Hz
i <sub>n</sub>	Current Noise Density	f = 1kHz	1.6		pA/√Hz
		f = 10Hz	3.1		pA/√Hz
V <sub>OS</sub>	Offset Voltage		±0.05	±0.7	mV (max)
ΔV <sub>OS</sub> /ΔTemp	Average Input Offset Voltage Drift vs Temperature	40°C ≤ T <sub>A</sub> ≤ 85°C	0.2		µV/°C
PSRR	Average Input Offset Voltage Shift vs Power Supply Voltage	ΔV <sub>S</sub> = 20V (Note 9)	125	110	dB (min)
I <sub>B</sub>	Input Bias Current	$V_{CM} = 0V$	7	72	nA (max)
ΔI <sub>OS</sub> /ΔTemp	Input Bias Current Drift vs Temperature	–40°C ≤ T <sub>A</sub> ≤ 85°C	0.1		nA/°C
I <sub>os</sub>	Input Offset Current	$V_{CM} = 0V$	5	65	nA (max)
V <sub>IN-CM</sub>	Common-Mode Input Voltage Range		+14.1 -13.9	(V+) - 2.0 (V-) + 2.0	V (min) V (min)
CMRR	Common-Mode Rejection	-10V <v<sub>CM&lt;10V</v<sub>	120	110	dB (min)
7	Differential Input Impedance		30		kΩ
Z <sub>IN</sub>	Common Mode Input Impedance	-10V <v<sub>CM&lt;10V</v<sub>	1000		MΩ
		–10V <v<sub>OUT&lt;10V, R<sub>L</sub> = 600Ω</v<sub>	140		dB
A <sub>VOL</sub>	Open Loop Voltage Gain	$-10V < V_{OUT} < 10V, R_{L} = 2k\Omega$	140	125	dB
		–10V <v<sub>OUT&lt;10V, R<sub>L</sub> = 10kΩ</v<sub>	140		dB

Symbol	Parameter	Conditions	LME	LME49710	
			Typical	Limit	Units (Limits)
			(Note 6)	(Notes 7, 8)	
		R <sub>L</sub> = 600Ω	±13.6	±12.5	V
V <sub>OUTMAX</sub>	Maximum Output Voltage Swing	$R_L = 2k\Omega$	±14.0		V
	$R_L = 10k\Omega$	±14.1		V	
I <sub>OUT</sub>	Output Current	R <sub>L</sub> = 600Ω, V <sub>S</sub> = ±17V	±26	±23	mA (min)
I <sub>OUT-CC</sub> Short Circuit Current	Short Circuit Current		+53		mA
		-42		mA	
		f <sub>IN</sub> = 10kHz			
R <sub>OUT</sub>	Output Impedance	Closed-Loop	0.01		Ω
		Open-Loop	13		Ω
C <sub>LOAD</sub>	Capacitive Load Drive Overshoot	100pF	16		%
I <sub>S</sub>	Quiescent Current	I <sub>OUT</sub> = 0mA	4.8	5.5	mA (max)

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

Note 2: Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: Amplifier output connected to GND, any number of amplifiers within a package.

Note 4: Human body model, 100pF discharged through a 1.5k $\Omega$  resistor.

Note 5: Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage and then discharged directly into the IC with no external series resistor (resistance of discharge path must be under 50Ω).

Note 6: Typical specifications are specified at +25°C and represent the most likely parametric norm.

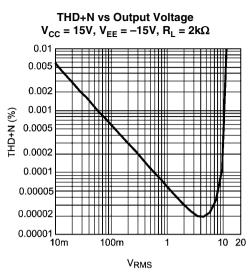
Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).

Note 8: Datasheet min/max specification limits are guaranteed by design, test, or statistical analysis.

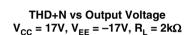
Note 9: PSRR is measured as follows:  $V_{OS}$  is measured at two supply voltages, ±5V and ±15V. PSRR =  $|20log(\Delta V_{OS}/\Delta V_S)|$ .

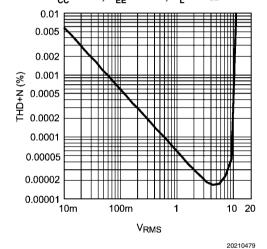


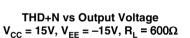
#### **Typical Performance Characteristics**

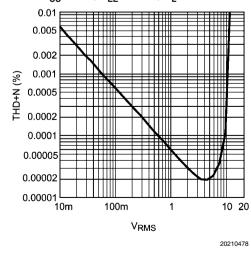


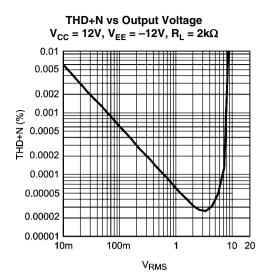






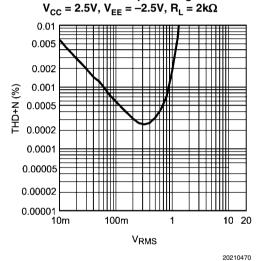




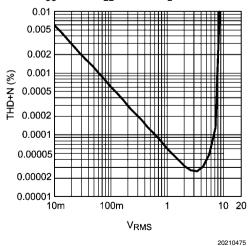


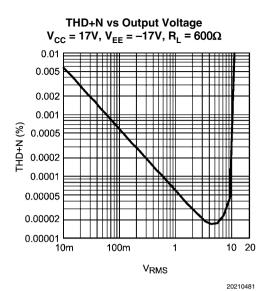
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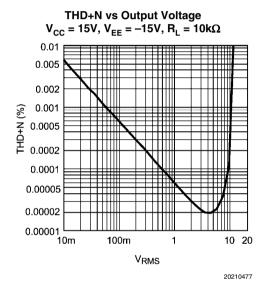
THD+N vs Output Voltage

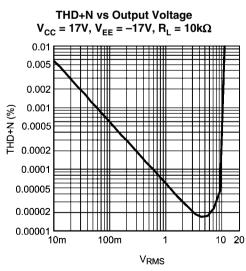


THD+N vs Output Voltage  $V_{CC} = 12V, V_{EE} = -12V, R_{L} = 600\Omega$ 

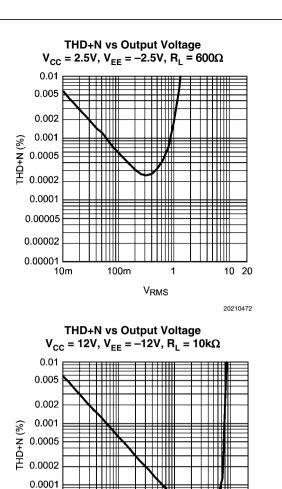


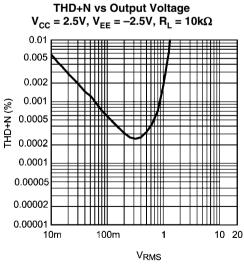












0.00005

0.00002 0.00001 L 10m 100m

1

VRMS

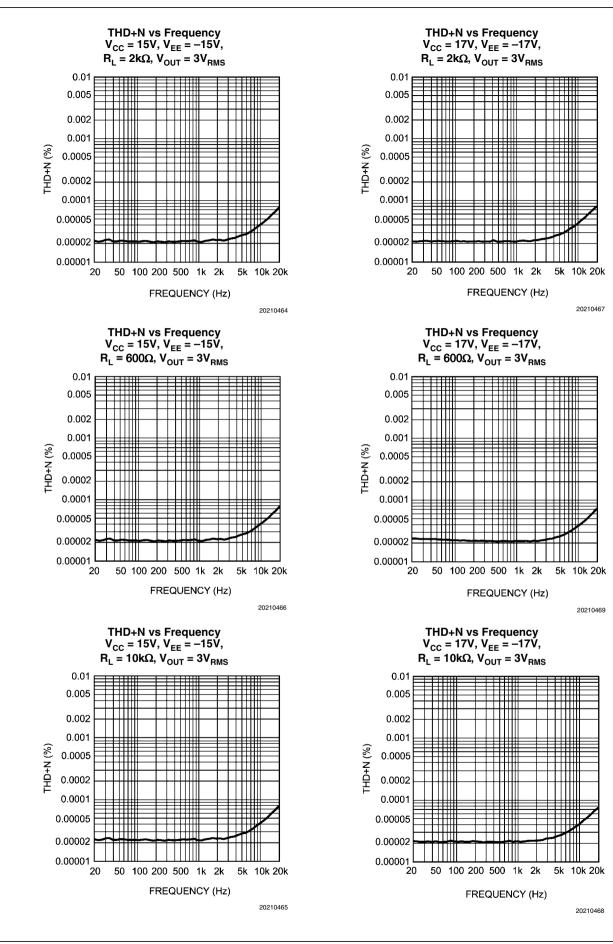


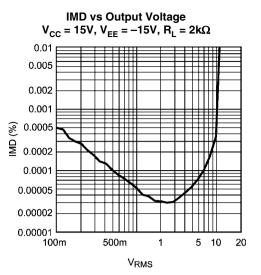
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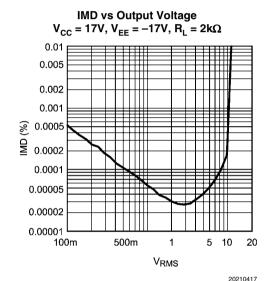
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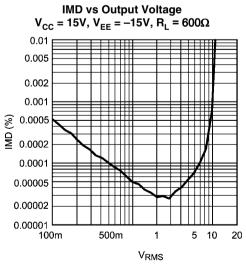
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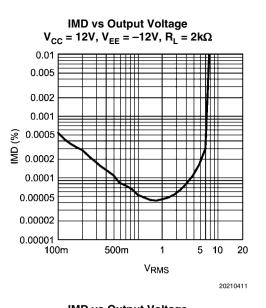


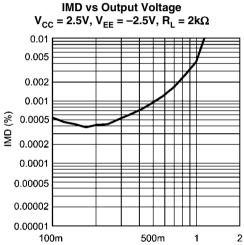


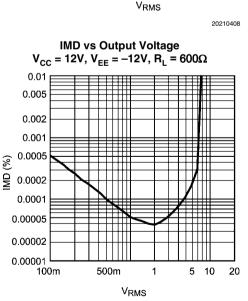




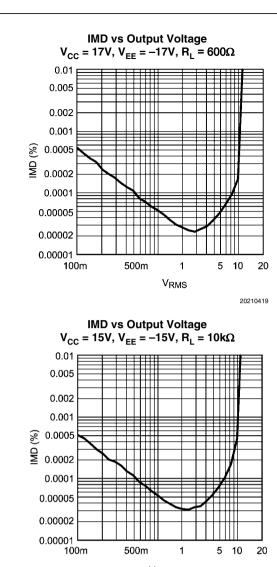


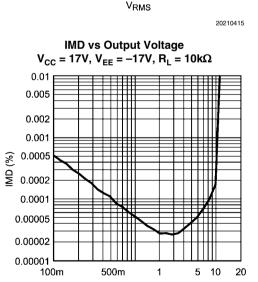




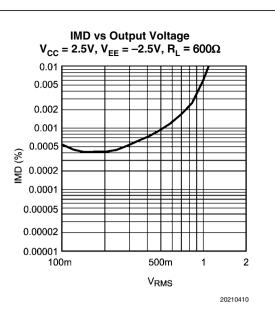


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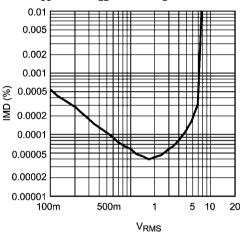


VRMS



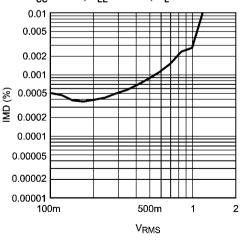
IMD vs Output Voltage

 $V_{CC} = 12V, V_{EE} = -12V, R_{L} = 10k\Omega$ 



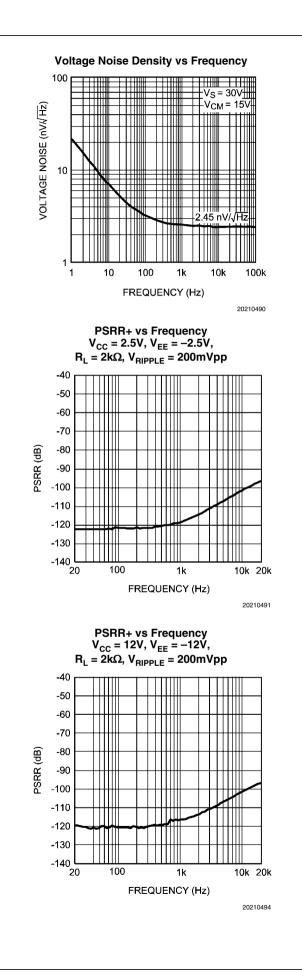
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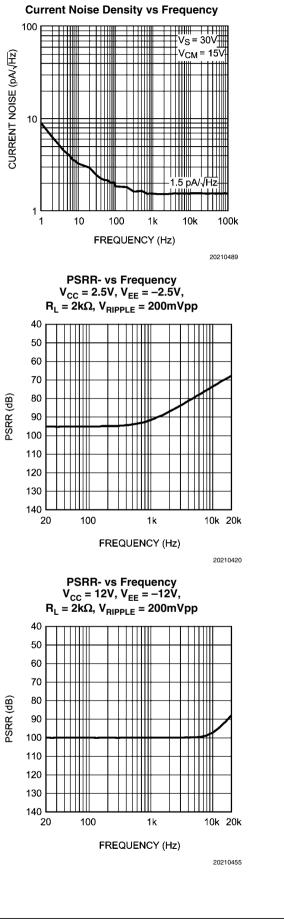
IMD vs Output Voltage V\_{CC} = 2.5V, V\_{EE} = -2.5V, R\_L = 10k\Omega

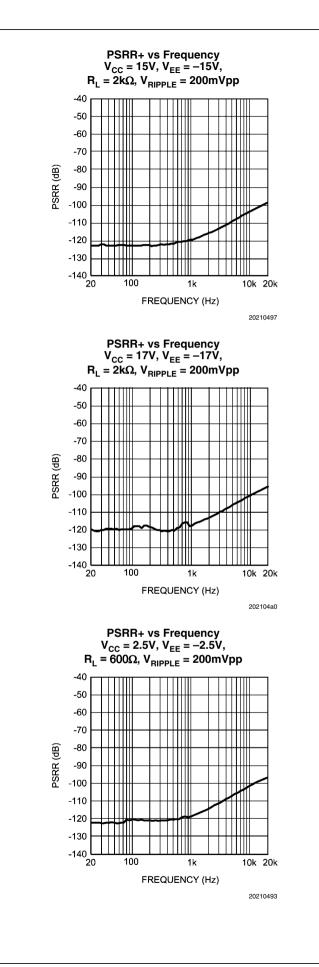


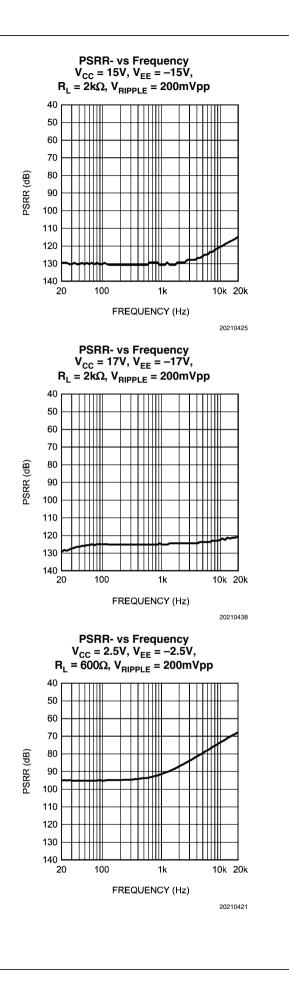
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1k

1k

10k 20k

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10k 20k

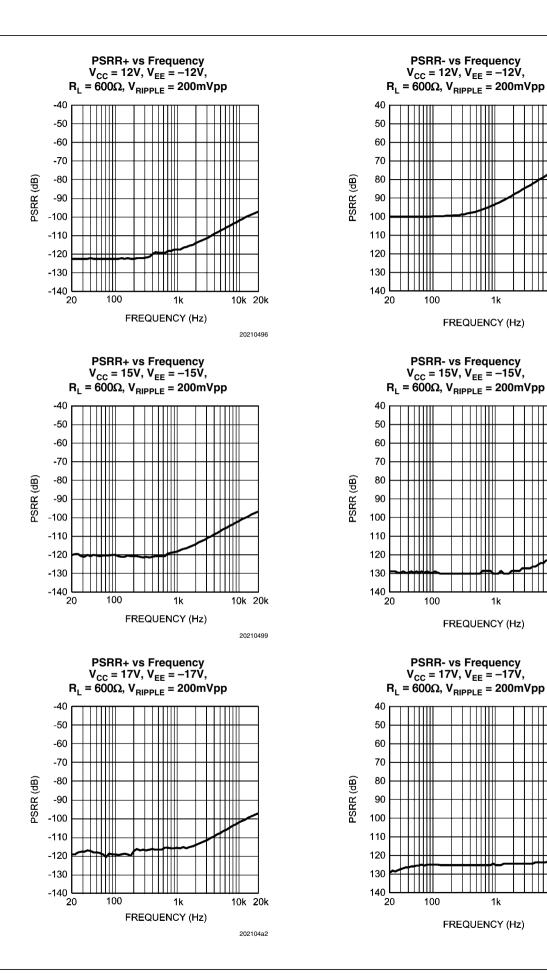
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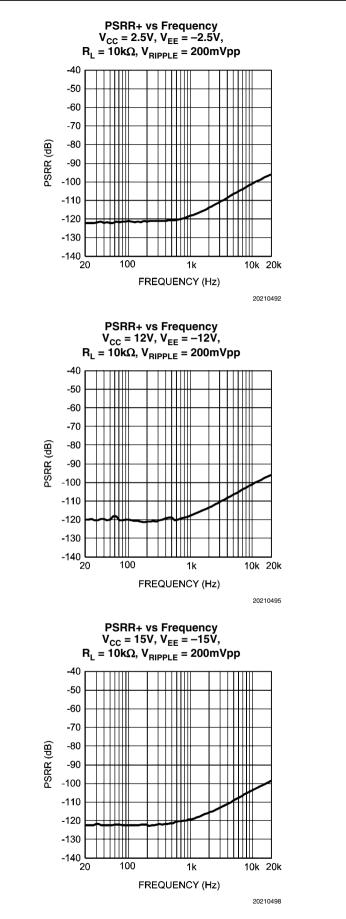
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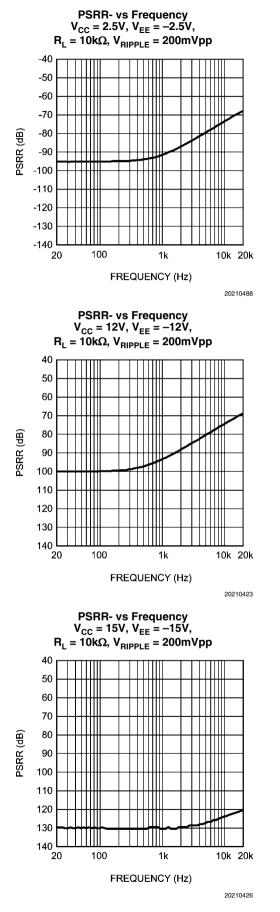
10k 20k

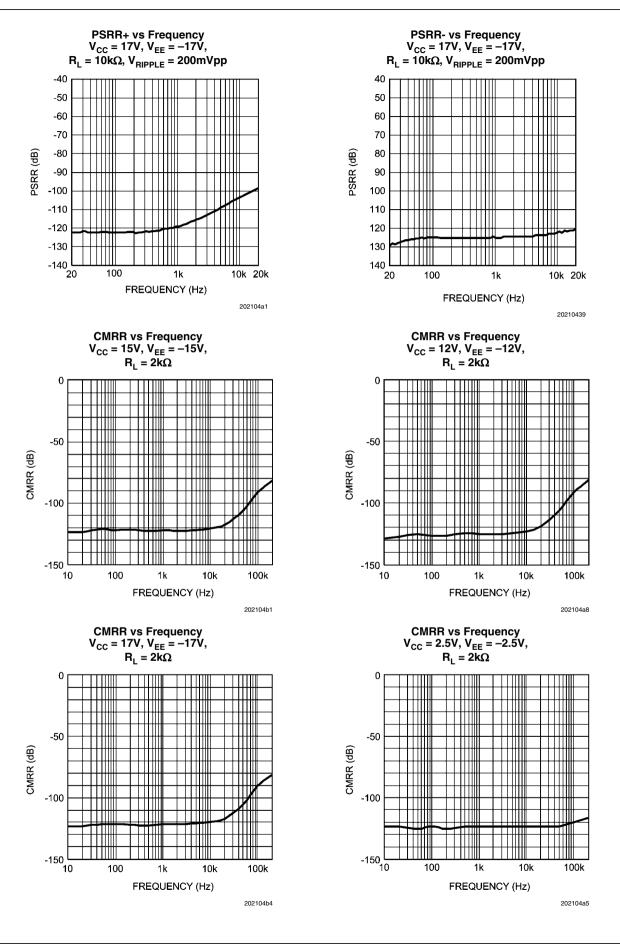
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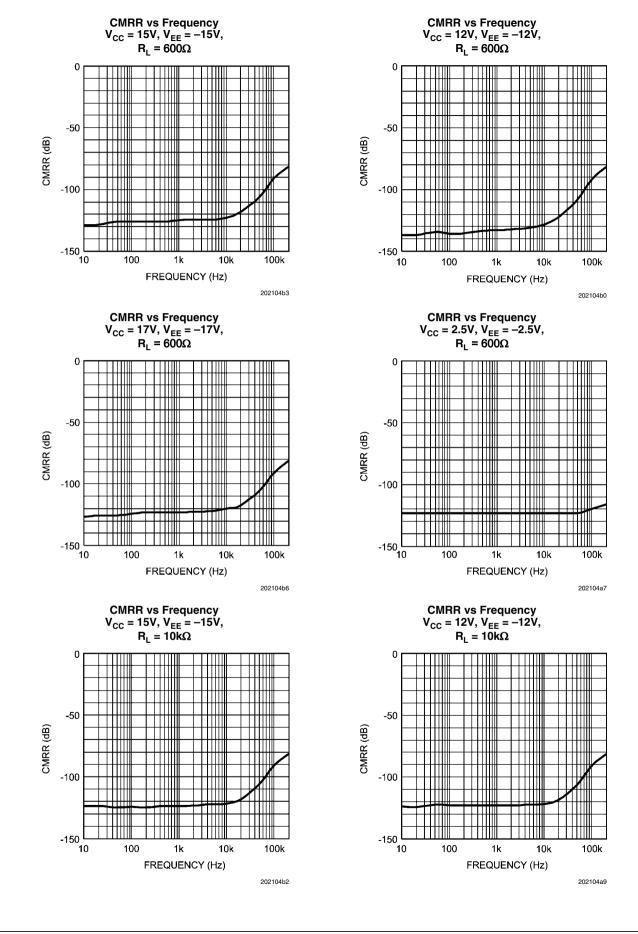
1k

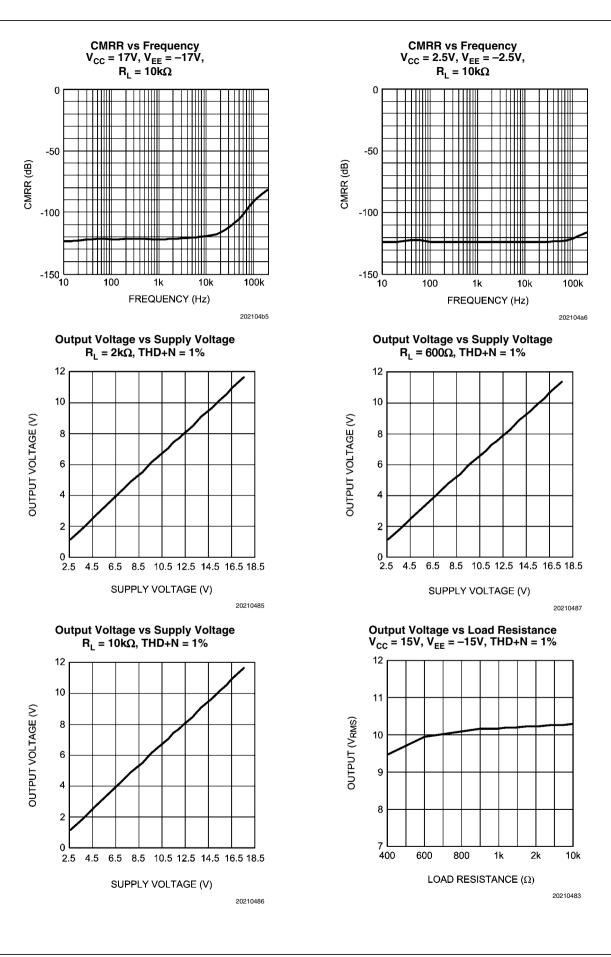


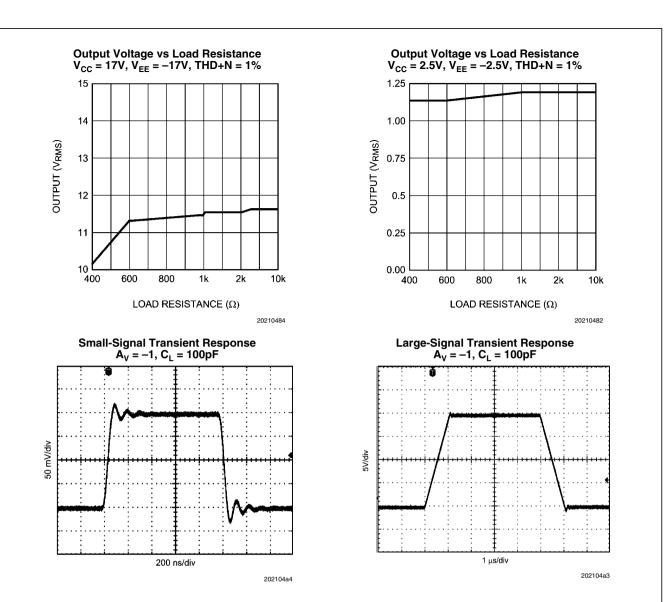












### **Application Hints**

The LME49710 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

#### **Noise Measurement Circuit**

40

30

20

10

ß

0

+1

-1 20

100

1k

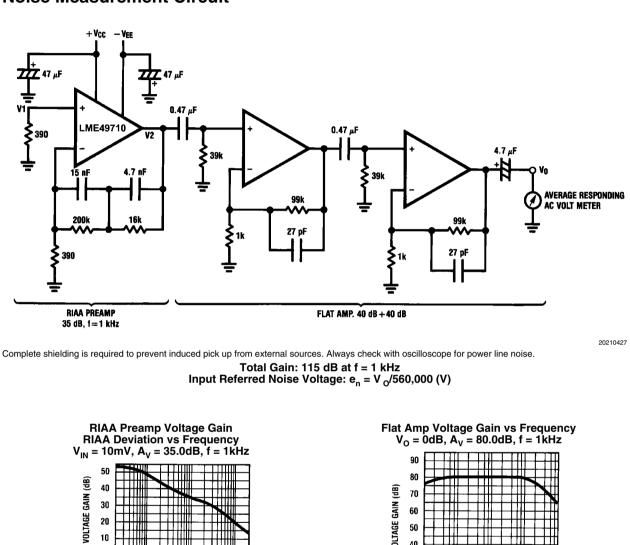
FREQUENCY (Hz)

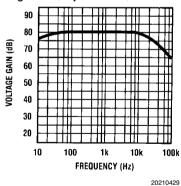
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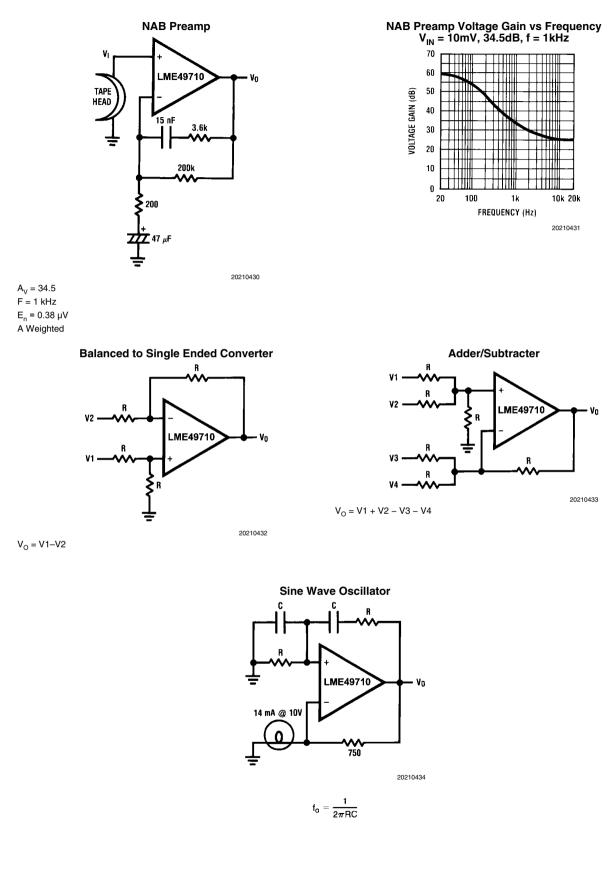
RIAA Deviation (db)

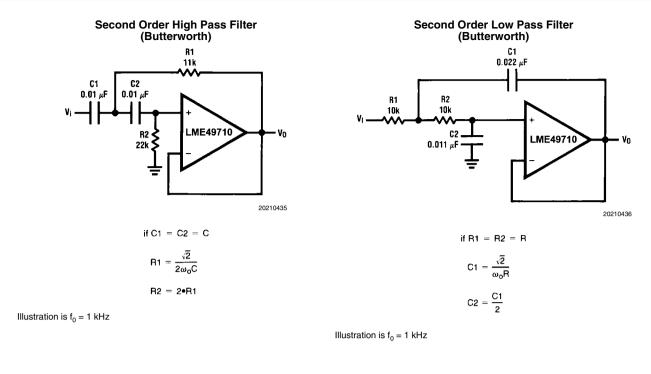
Capacitive loads greater than 100pF must be isolated from the output. The most straight forward way to do this is to put a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

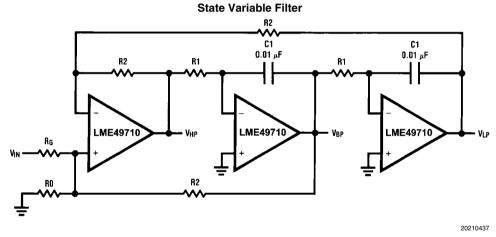




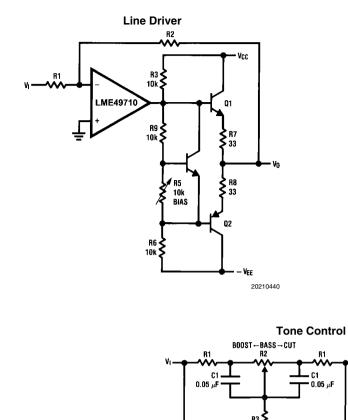
## **Typical Applications**

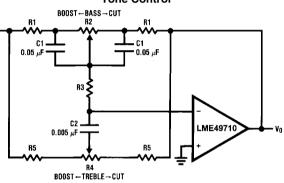




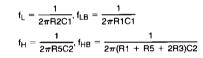


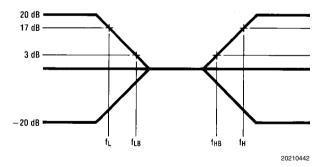
$$f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2} \left( 1 + \frac{R2}{R0} + \frac{R2}{RG} \right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$$

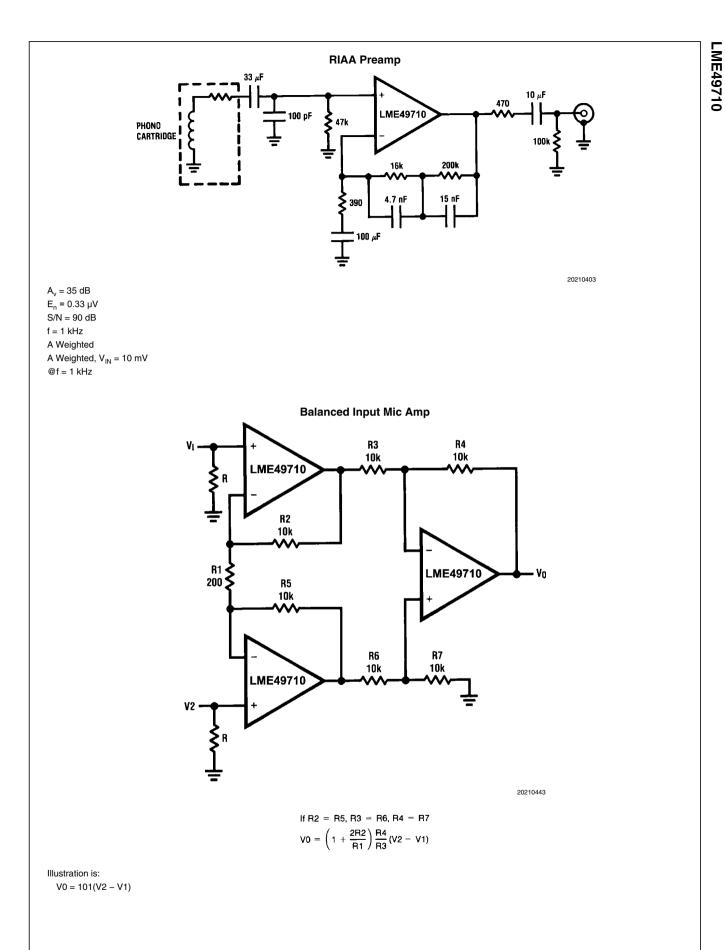




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### **Application Information**

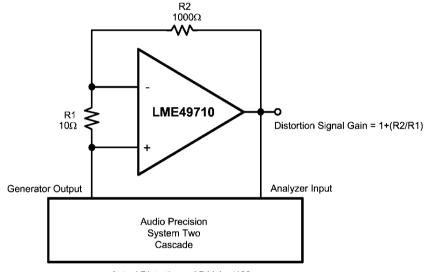
#### DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49710 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49710's low residual distortion is an input referred internal error. As shown in Figure 2, adding the  $10\Omega$  resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 2.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.



Actual Distortion = AP Value/100

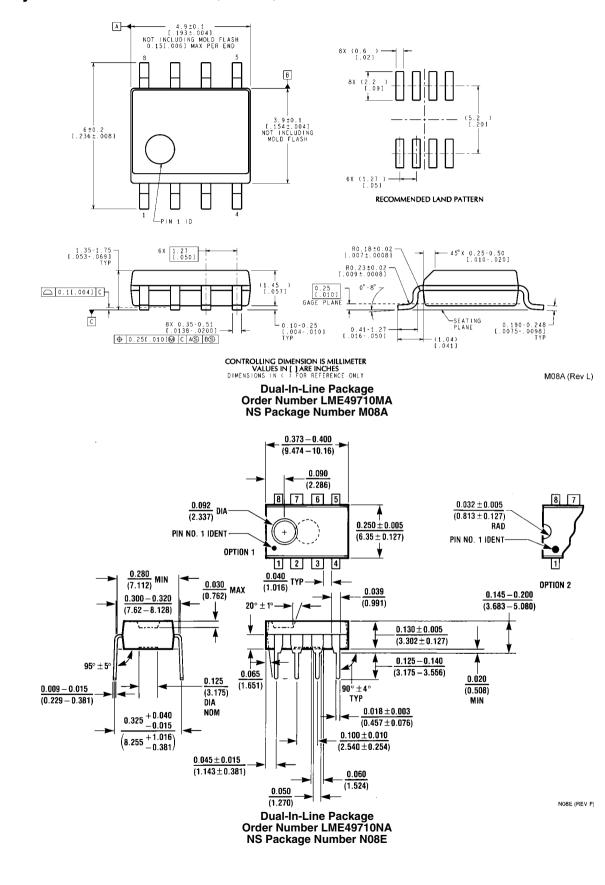
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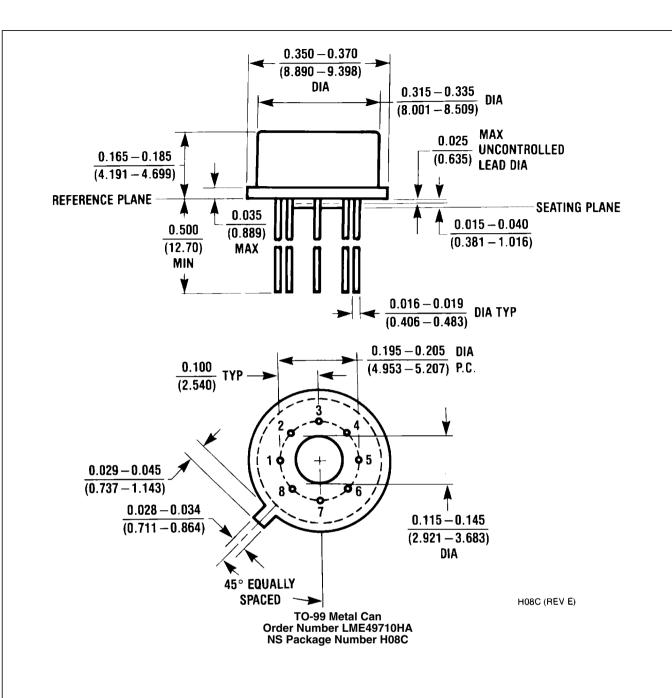
#### FIGURE 2. THD+N and IMD Distortion Test Circuit

## **Revision History**

Rev	Date	Description
1.0	11/16/07	Initial release.
1.1	12/12/06	Added the Typical Performance curves.
1.2	01/15/07	Added more curves and input some text edits.
1.3	03/09/07	Fixed graphics 20210489 and 90.

#### Physical Dimensions inches (millimeters) unless otherwise noted





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